

ABSTRACT

5 An object of the present invention is to provide a
flip-chip-type gallium nitride compound semiconductor
light-emitting device exhibiting excellent ohmic
characteristics, excellent bonding characteristics, and
high emission output.

10 The inventive flip-chip-type gallium nitride
compound semiconductor light-emitting device comprises a
substrate, an n-type semiconductor layer, a light-
emitting layer, a p-type semiconductor layer, a negative
electrode provided on the n-type semiconductor layer, and
a positive electrode provided on the p-type semiconductor
layer, the layers being successively provided atop the
15 substrate in this order and being composed of a gallium
nitride compound semiconductor, wherein the positive
electrode has a three-layer structure comprising an ohmic
electrode layer which is in contact with the p-type
semiconductor layer, an adhesion layer which is provided
20 on the ohmic electrode layer, and a bonding pad layer
provided on the adhesion layer, each melting point of
these layers being lowered in this order.